N-Channel Enhancement Mode Power MOSFET

MTE080N15Q8

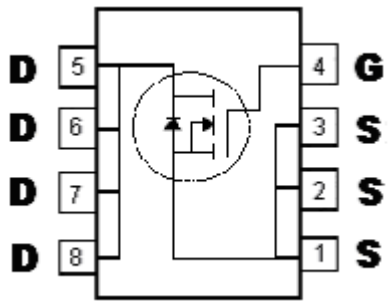
BV_{DSS}	**150V**
I_D @ T_A=25°C, V_{GS}=10V	**4A**
$R_{DS(ON)}$@V_{GS}=10V, I_D=4A	**77 mΩ (typ)**
$R_{DS(ON)}$@V_{GS}=6V, I_D=3.3A	**82 mΩ (typ)**

Features

- Single Drive Requirement
- Low On-resistance
- Fast Switching Characteristic
- Pb-free & Halogen-free package

Symbol

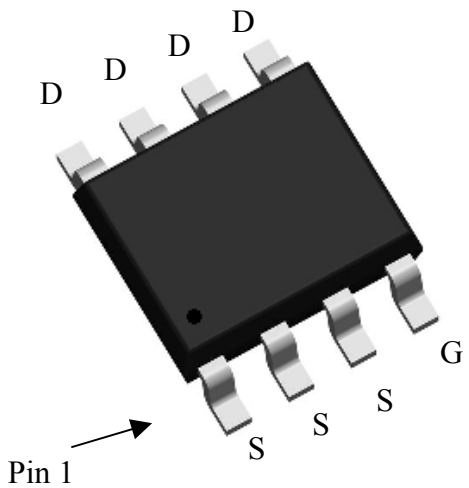
MTE080N15Q8



G：Gate D：Drain S：Source

Outline

SOP-8



Ordering Information

Device	Package	Shipping
MTE080N15Q8-0-T3-G	SOP-8 (RoHS compliant & Halogen-free package)	2500 pcs / Tape & Reel

Environment friendly grade : S for RoHS compliant products, G for RoHS compliant and green compound products

Packing spec, T3 : 2500 pcs / tape & reel, 13” reel

Product rank, zero for no rank products

Product name

Absolute Maximum Ratings (Tc=25°C, unless otherwise noted)

Parameter		Symbol	Limits	Unit
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current @ T_A=25°C, V_{GS}=10V		I_D	4	A
Continuous Drain Current @ T_A=70°C, V_{GS}=10V			3.2	
Pulsed Drain Current		I_{DM}	20 *1	
Avalanche Current @ L=0.1mH		I_{AS}	8	
Avalanche Energy @ L=1mH, I_D=8A, V_{DD}=30V		E_{AS}	32 *3	mJ
Repetitive Avalanche Energy @ L=0.05mH		E_{AR}	1.6 *2	
Total Power Dissipation	T_A=25 °C	P_D	3.1	W
	T_A=70 °C		2	
Operating Junction and Storage Temperature		Tj, Tstg	-55~+150	°C

Note : *1. Pulse width limited by maximum junction temperature
*2. Duty cycle ≤ 1%
*3. 100% tested by conditions of L=0.5mH, I_{AS}=3A, V_{GS}=10V, V_{DD}=50V

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case	$R_{\theta JC}$	20	°C/W
Thermal Resistance, Junction-to-ambient (Note)	$R_{\theta JA}$	40	

Note : 40°C / W when mounted on a 1 in^2 pad of 2 oz copper, t≤10s; 125°C/W when mounted on minimum pad.

Characteristics (T_C=25°C, unless otherwise specified)

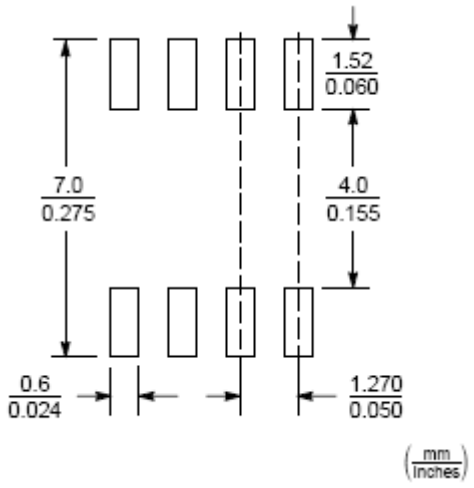
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	150	-	-	V	V_{GS}=0V, I_D=250μA
$V_{GS(th)}$	2	-	4		V_{DS} = V_{GS}, I_D=250μA
G_{FS}	-	7.7	-	S	V_{DS} =10V, I_D=3A
I_{GSS}	-	-	±100	nA	V_{GS}=±20V, V_{DS}=0V
I_{DSS}	-	-	1	μA	V_{DS} =120V, V_{GS} =0V
	-	-	25		V_{DS} =120V, V_{GS} =0V, Tj=125°C
*$R_{DS(ON)}$	-	77	100	mΩ	V_{GS} =10V, I_D=4A
	-	82	120		V_{GS} =6V, I_D=3.3A
Dynamic					
Qg *1, 2	-	33.7	50	nC	V_{DS}=120V, V_{GS}=10V, I_D=4A
Qgs *1, 2	-	7.1	-		
Qgd *1, 2	-	11.9	-		
Ciss	-	683	-	pF	V_{DS}=100V, V_{GS}=0V, f=1MHz
Coss	-	53	-		
Crss	-	24	-		

Characteristics (Cont. T_C=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dynamic					
$t_{d(ON)}$ *1, 2	-	10.6	-	ns	V_{DS}=75V, I_D=1A, V_{GS}=10V, R_{GS}=3Ω
tr *1, 2	-	17.6	-		
$t_{d(OFF)}$ *1, 2	-	33.4	-		
t_f *1, 2	-	34.2	-		
Rg	-	3.6	-	Ω	f=1MHz
Source-Drain Diode Ratings and Characteristics					
I_S *1	-	-	4	A	
I_{SM} *3	-	-	16		
V_{SD} *1	-	0.75	1.2	V	I_S=2.3A, V_{GS}=0V
trr	-	34	-	ns	I_F=2.3A, dI_F/dt=100A/μs
Qrr	-	55	-	nC	

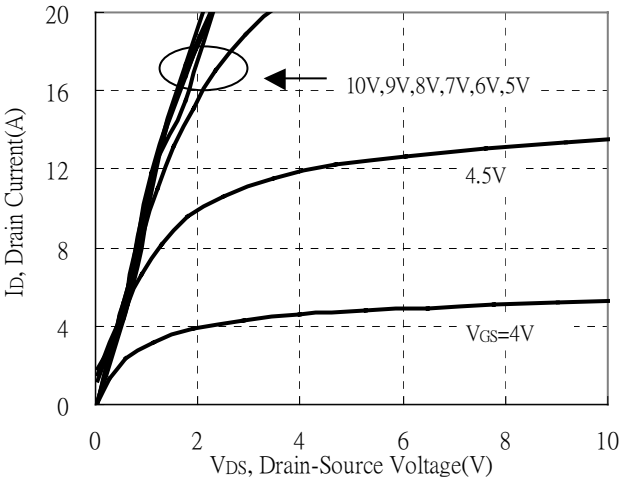
Note : *1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%
*2.Independent of operating temperature
*3.Pulse width limited by maximum junction temperature.

Recommended Soldering Footprint

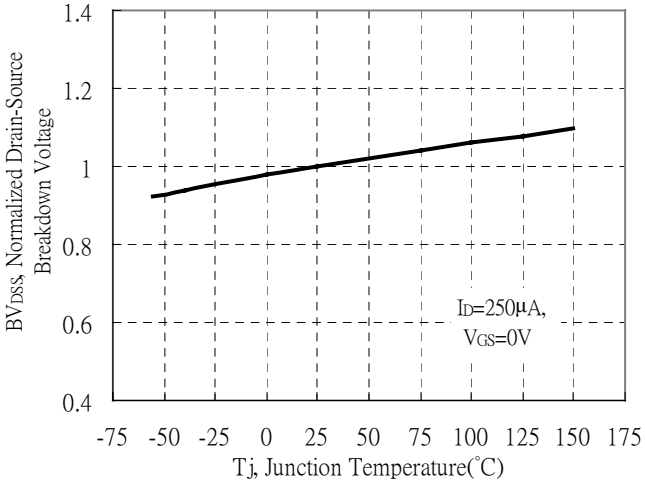


Typical Characteristics

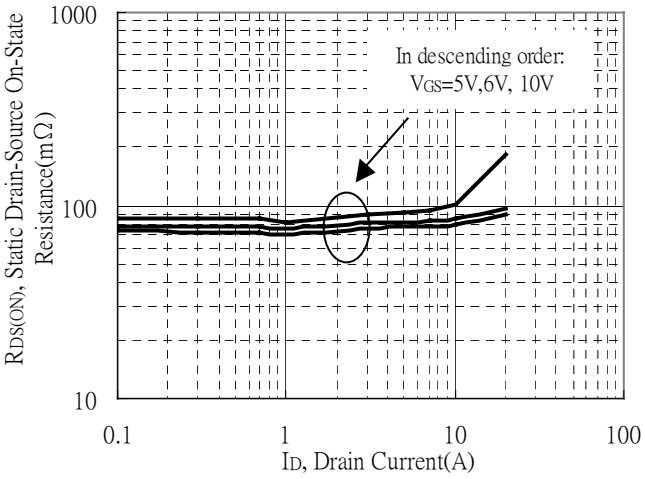
Typical Output Characteristics



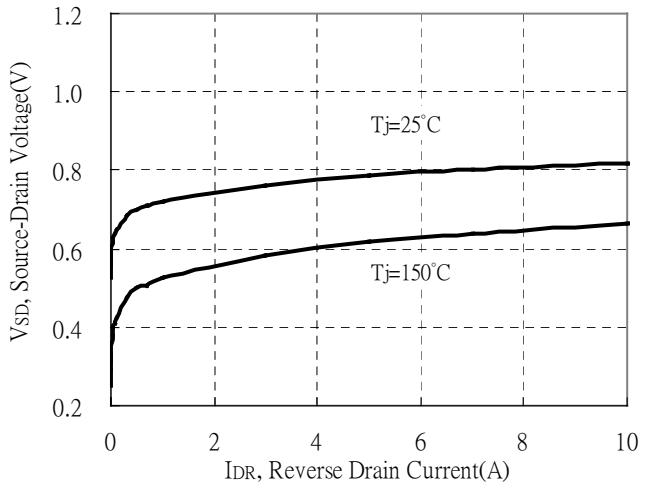
Brekdown Voltage vs Ambient Temperature



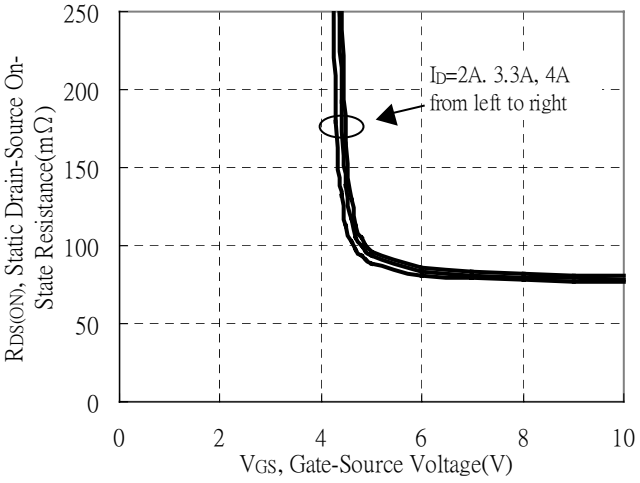
Static Drain-Source On-State resistance vs Drain Current



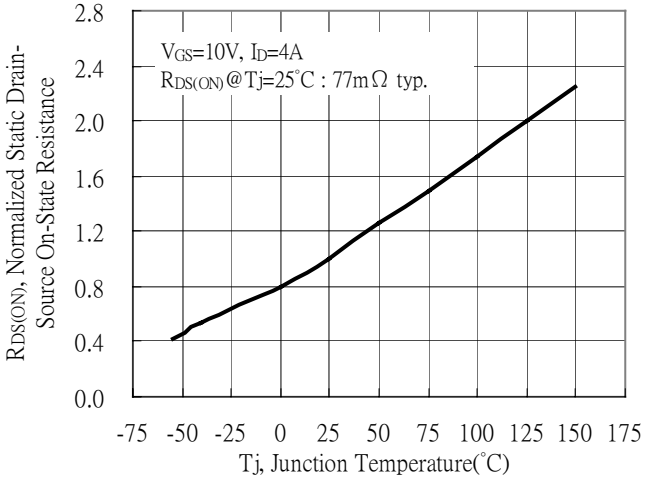
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

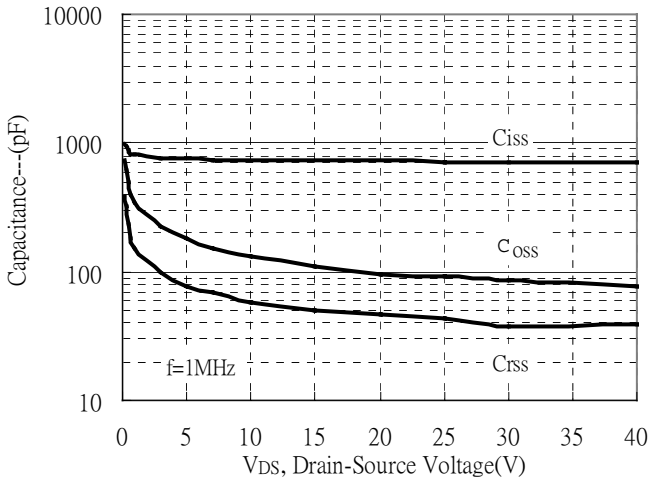


Drain-Source On-State Resistance vs Junction Tempearture

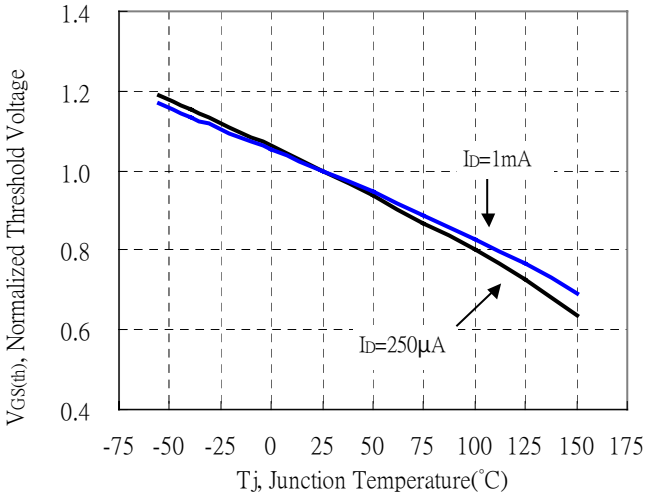


Typical Characteristics(Cont.)

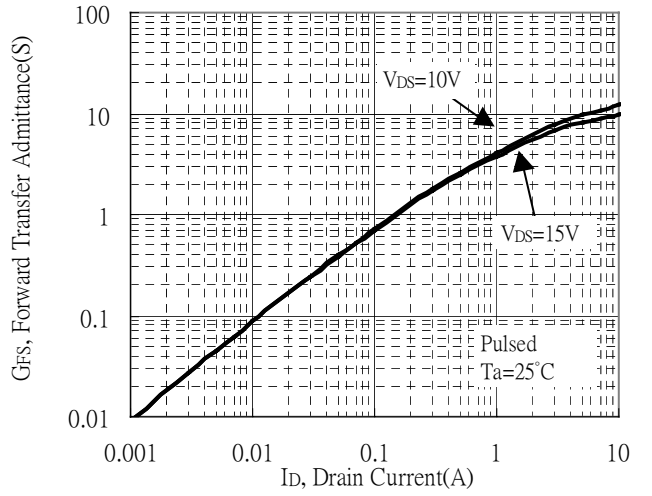
Capacitance vs Drain-to-Source Voltage



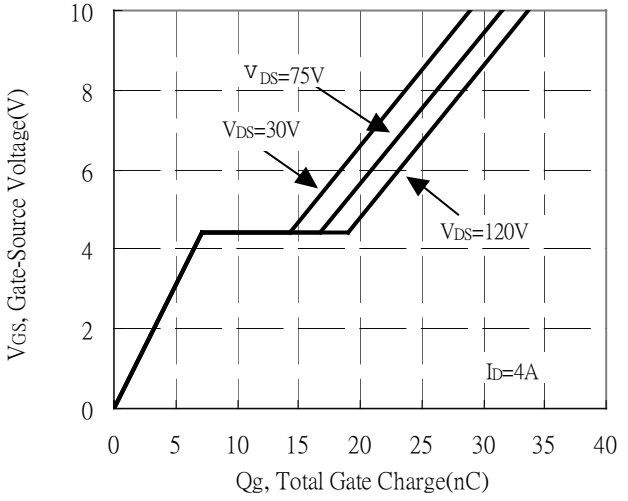
Threshold Voltage vs Junction Tempearture



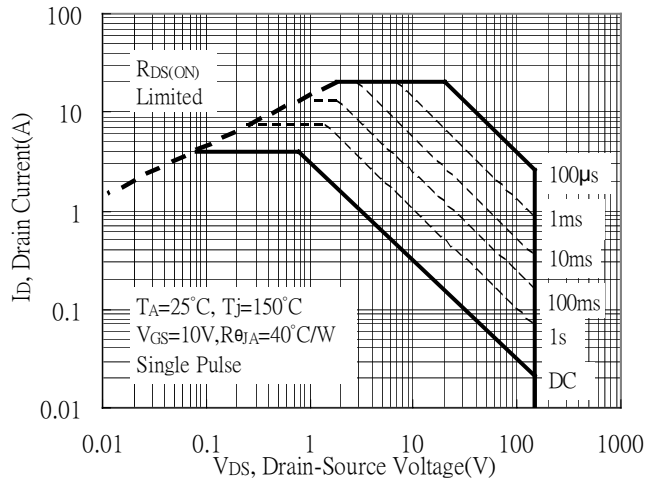
Forward Transfer Admittance vs Drain Current



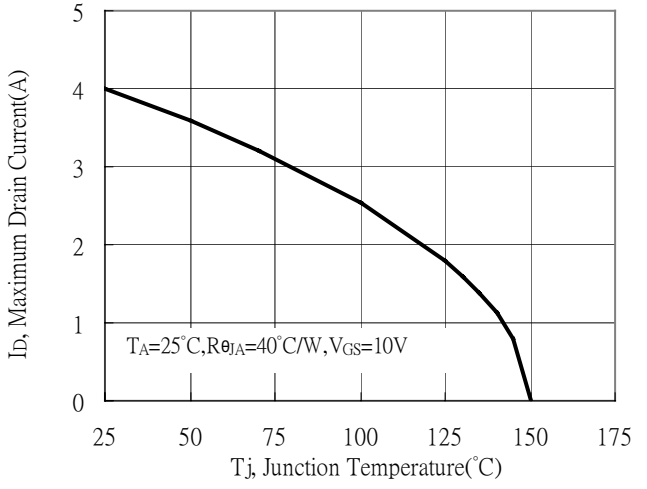
Gate Charge Characteristics



Maximum Safe Operating Area

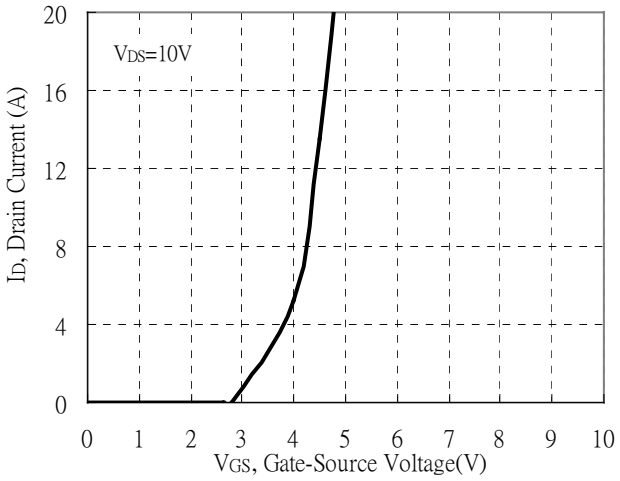


Maximum Drain Current vs Junction Temperature

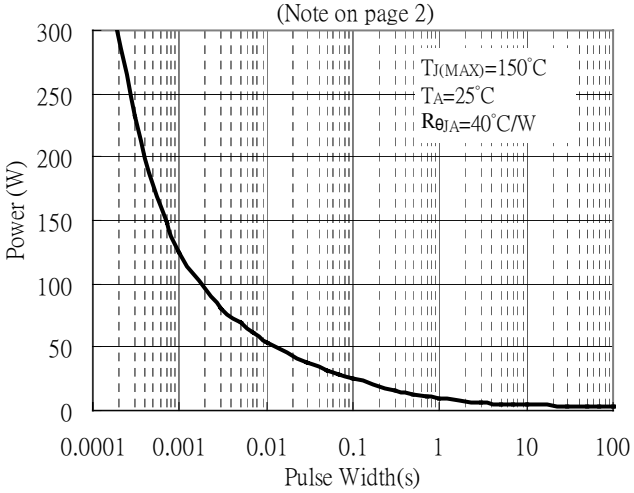


Typical Characteristics(Cont.)

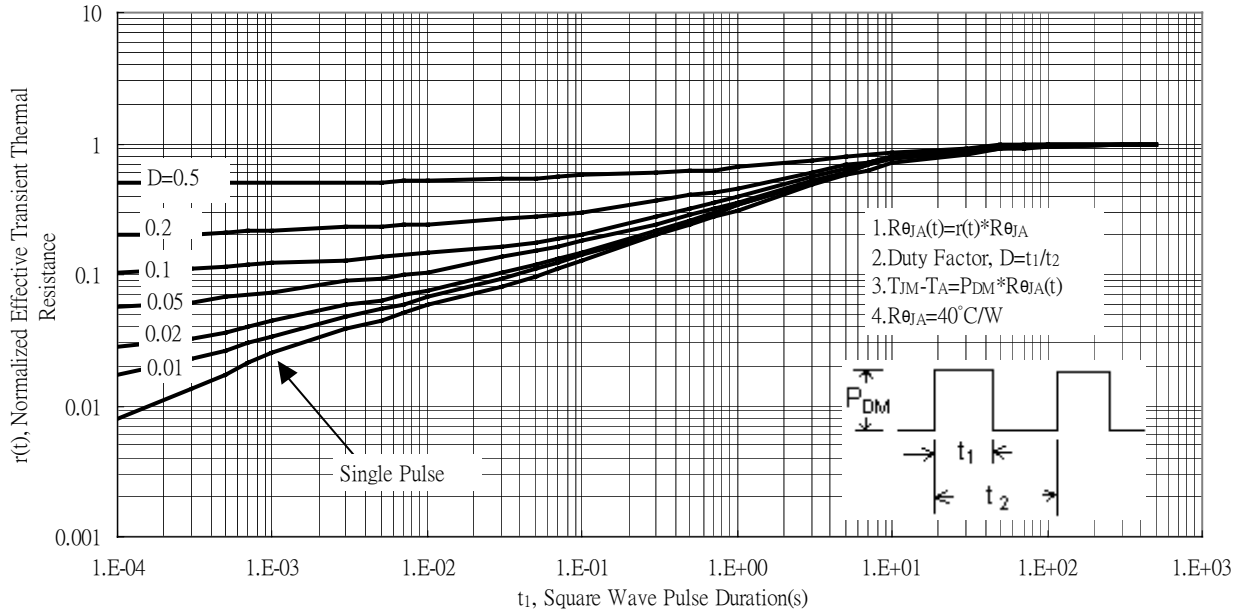
Typical Transfer Characteristics



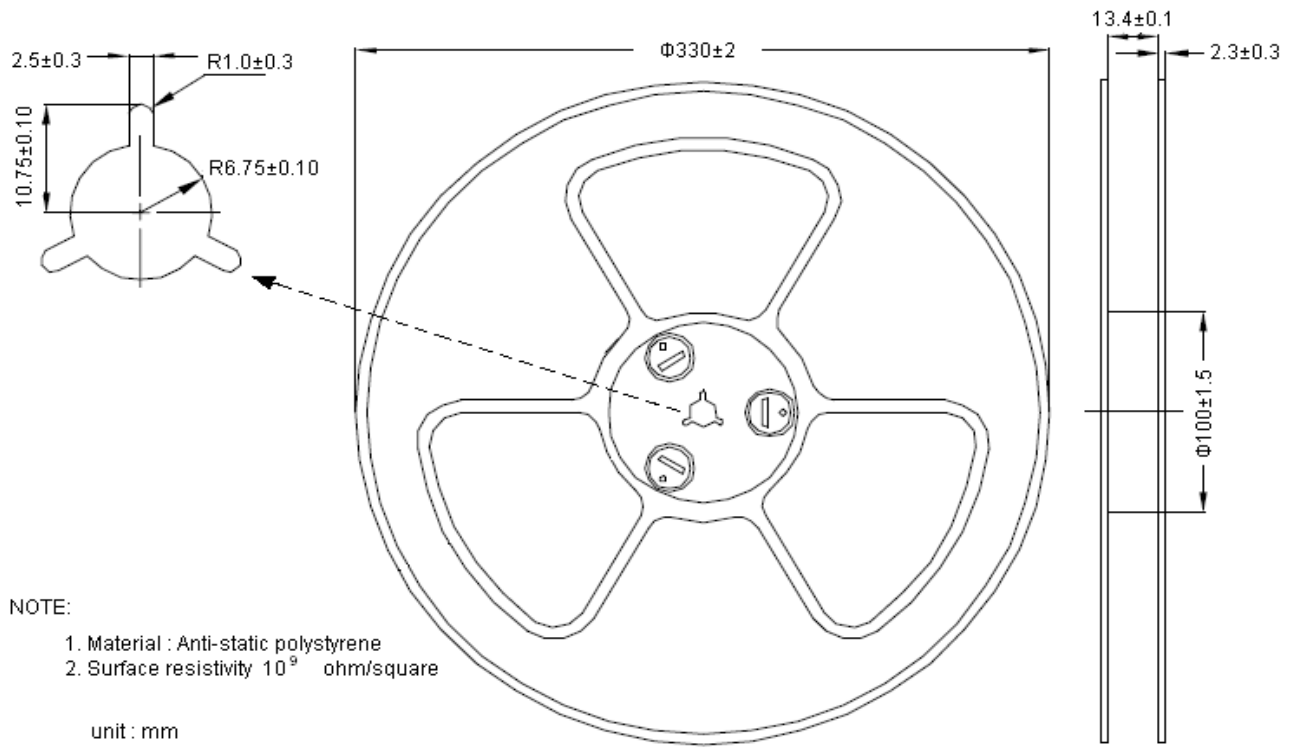
Single Pulse Power Rating, Junction to Ambient
(Note on page 2)



Transient Thermal Response Curves



Reel Dimension

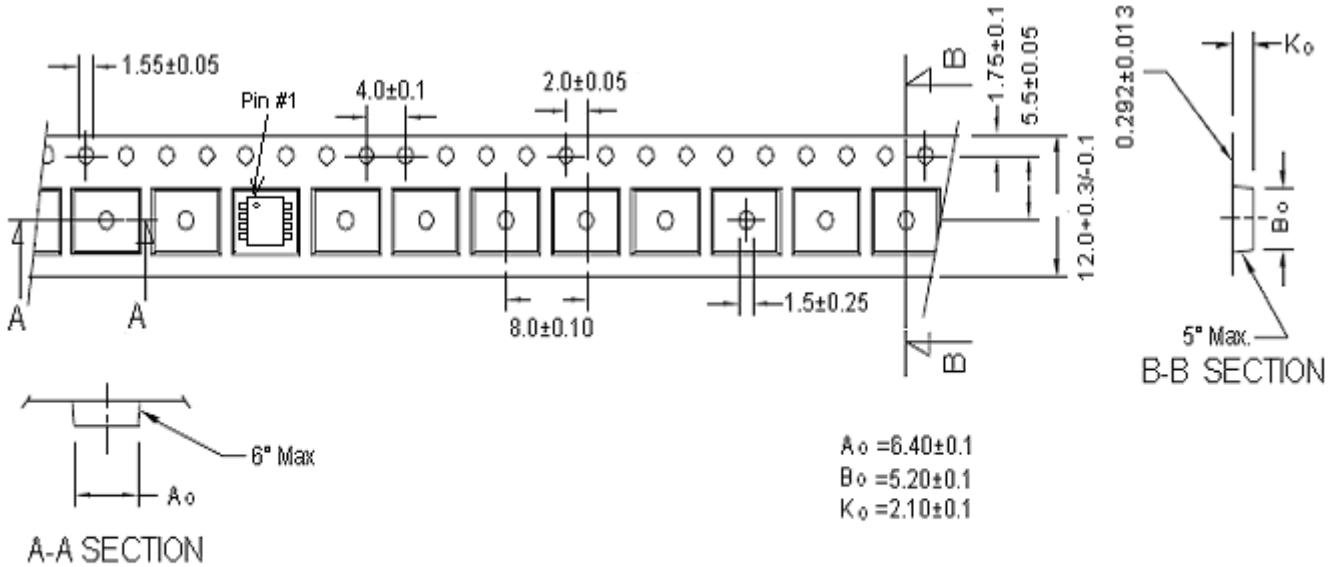


NOTE:

1. Material : Anti-static polystyrene
2. Surface resistivity 10^9 ohm/square

unit : mm

Carrier Tape Dimension



Notes:

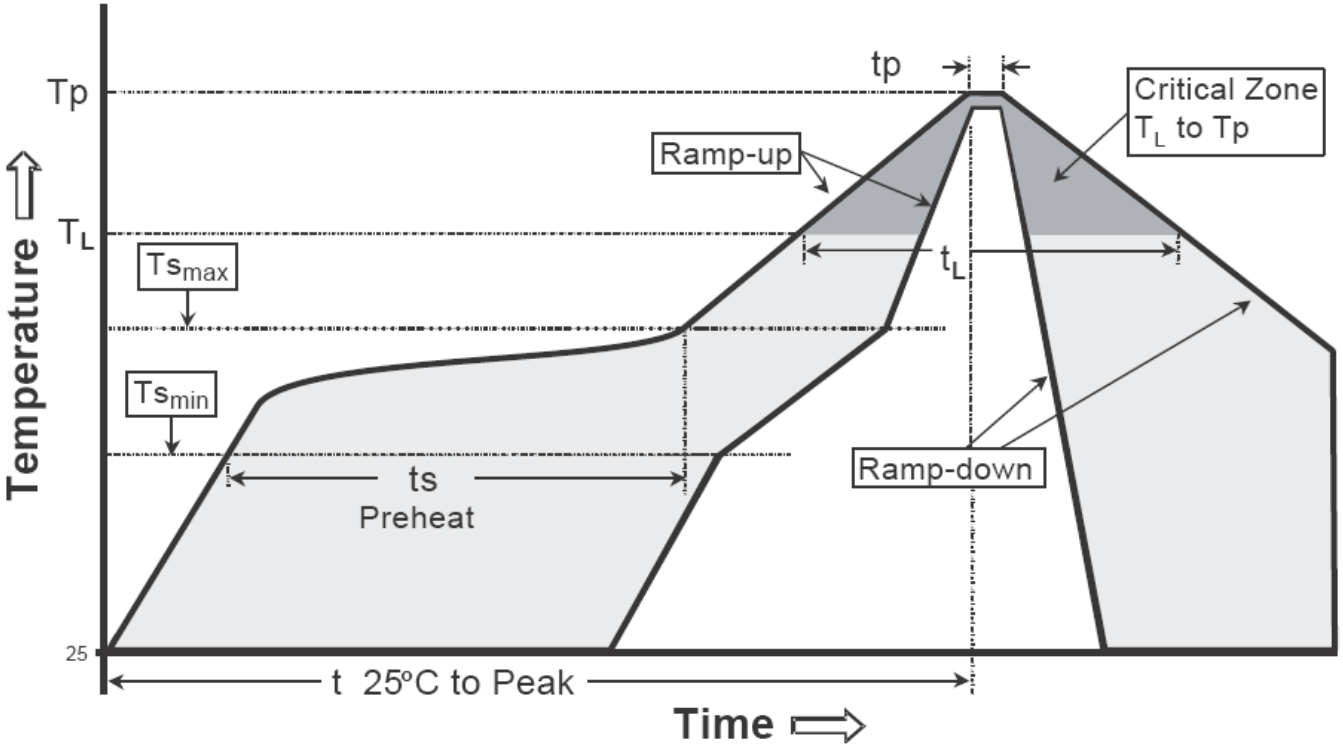
1. 10 sprocket hole pitch cumulative tolerance ±0.2.
2. Camber not to exceed 1mm in 100mm.
3. Material: conductive black polystyrene
4. Ao & Bo measured on a plane 0.3mm above the bottom of the pocket.
5. Ko measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Uni : millimeter

Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

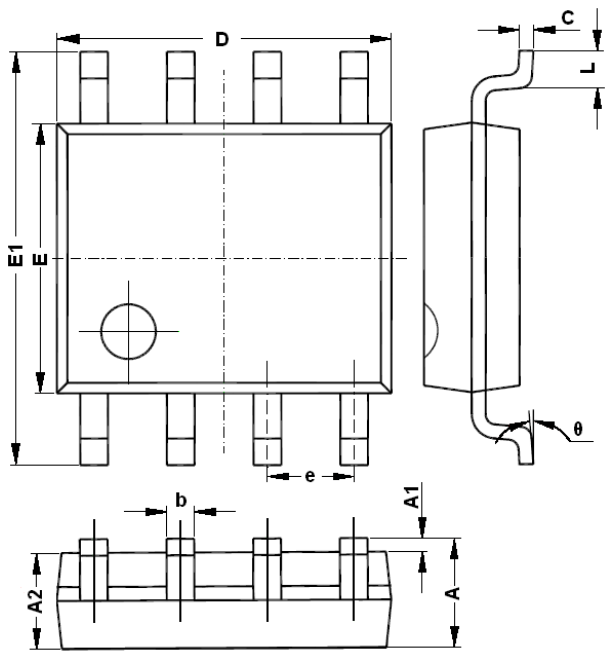
Recommended temperature profile for IR reflow



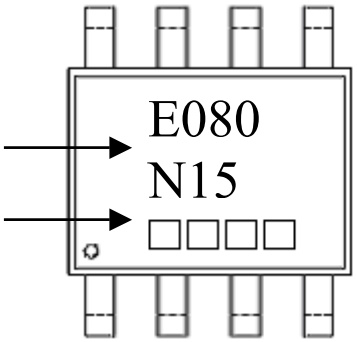
Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat −Temperature Min(T_S min) −Temperature Max(T_S max) −Time($t_{s\ min}$ to $t_{s\ max}$)	 100°C 150°C 60-120 seconds	 150°C 200°C 60-180 seconds
Time maintained above: −Temperature (T_L) − Time (t_L)	 183°C 60-150 seconds	 217°C 60-150 seconds
Peak Temperature(T_P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note :1. All temperatures refer to topside of the package, measured on the package body surface.
2.For devices mounted on FR-4 PCB of 1.6mm or equivalent grade PCB. If other grade PCB is used, care should be taken to match the coefficients of thermal expansion between components and PCB. If they are not matched well, the solder joints may crack or the bodies of the parts may crack or shatter as the assembly cools.

SOP-8 Dimension



Marking:



Date Code(counting from left to right) :
1st code: year code, the last digit of Christian year
2nd code : month code, Jan→A, Feb→B, Mar→C, Apr→D
May→E, Jun→F, Jul→G, Aug→H, Sep→J,
Oct→K, Nov→L, Dec→M
3rd and 4th codes : prodcution serial number, 01~99

8-Lead SOP-8 Plastic Package
CYStek Package Code: Q8

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069	E	3.800	4.200	0.150	0.165
A1	0.100	0.250	0.004	0.010	E1	5.800	6.200	0.228	0.244
A2	1.350	1.550	0.053	0.061	e	1.270 (BSC)		0.050 (BSC)	
b	0.330	0.510	0.013	0.020	L	0.300	1.270	0.012	0.050
c	0.170	0.250	0.006	0.010	θ	0	8°	0	8°
D	4.700	5.100	0.185	0.200					

Notes: 1.Controlling dimension: millimeters.
2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of CYStek.
- CYStek reserves the right to make changes to its products without notice.
- CYStek ***semiconductor products are not warranted to be suitable for use in Life-Support Applications, or systems.***
- CYStek assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.